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Group No. 2826
Examiner: Mandala, Victor A.
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marked version of claims 1-6 showing the changes made to the old set of claims
attached as appendix B.



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1. (Once amended)

A Thin-Film Transistor array structure, comprising:

- a Thin-Film Transistor;
- a data line coupled to a drain electrode of the Thin-Film Transistor;
- a scanning line coupled to a gate electrode of the Thin-Film Transistor and crossed to the data line to form a plurality of rectangular pixels in matrix;
- a pixel electrode formed at each of the pixels and coupled to a source electrode of the Thin-Film Transistor, the pixel electrode having an edge; and
- an auxiliary electrode coupled to the pixel electrode, wherein the edge of the pixel electrode is disposed on the auxiliary electrode.

2. (Once amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein a pattern constructed by the auxiliary electrode, the source electrode and the data line is designed as a mask.

3. (Once amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the auxiliary electrode is formed in an H-shaped pattern.

4. (Once amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the pixel electrode is coupled to the source electrode via a contact hole.

5. (Once amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the auxiliary electrode is coupled to the pixel electrode via a contact hole.



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6. (Once amended)

A Thin-Film Transistor array structure, comprising:

- a Thin-Film Transistor;
- a data line coupled to a drain electrode of the Thin-Film Transistor;
- a scanning line coupled to a gate electrode of the Thin-Film Transistor and crossed to the data line to form a plurality of rectangular pixels in matrix; and
- a pixel electrode formed at each of the pixels and coupled to a source electrode of the Thin-Film Transistor via a contact hole, wherein the edge of the pixel electrode is disposed on the source electrode which is extended to the region where the pixel electrode is next to the data line.

10. (New)

A Thin-Film Transistor array structure, comprising:

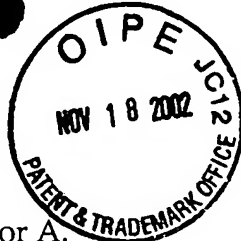
- a Thin-Film transistor having a drain electrode, a gate electrode and a source electrode;
- a data line coupled to the drain electrode;
- a scanning line coupled to the gate electrode and crossed to the data line to form a plurality of rectangular pixels in matrix;
- a pixel electrode formed at each of the pixels and coupled to the source electrode, the pixel electrode having an edge region which is closest to the data line; and
- an auxiliary electrode coupled to the pixel electrode, wherein the edge region is disposed on the auxiliary electrode.

11. (New)

A Thin-Film Transistor array structure, comprising:

- a Thin-Film Transistor having a drain electrode, a gate electrode and a source electrode;

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a data line coupled to the drain electrode;

a scanning line coupled to the gate electrode and crossed to the data line to form a plurality of rectangular pixels in matrix;

a pixel electrode formed at each of the pixels and coupled to the source electrode via a contact hole, the pixel electrode having an edge region which is closest to the data line,

wherein the source electrode comprises an extended portion extended to a region corresponding to the edge region of the pixel electrode, and the edge region of the pixel electrode is disposed on the extended portion of the source electrode.